



10V Drive Nch MOSFET

RDD020N60

[Product description]

Power MOSFETs are made as low ON-resistance devices by the micro-processing technologies useful for wide range of applications. Broad lineup covering compact types, high-power types and complex types to meet various needs in the market.

Features

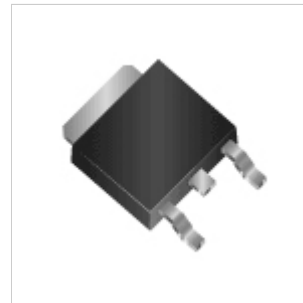
E10V-drive type Nch Power MOSFET

Product specifications

Absolute maximum ratings (Ta=25°C)

Rated parameters	Standard value	Conditions
Drain-Source voltage $V_{DSS}(V)$	600	
Gate-Source voltage $V_{GSS}(V)$	± 30	
Drain current (continuous) $I_D(A)$	± 2.0	Limited only by maximum channel temperature allowed
Source current(body Di) $I_S(A)$	2	
Total power dissipation $P_D(W)$	20	Tc=25°C
Channel temperature Tch(°C)	150	
Storage temperature Tstg(°C)	-55 to +150	

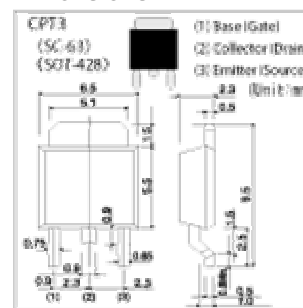
Outline



CPT3/SC-63/SOT-428

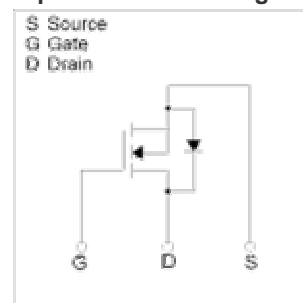
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Dimensions



* Click to enlarge.

Equivalent circuit diagram



*The contents described here are just outline for introduction.

Please obtain the specification sheets from us for thorough check before use.

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